



Electrically-based spin switching in hetero-dimensional quantum dot device

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Overview

- **Back Ground**

- ***Introduction of single electron transistor***

- ***Introduction of 2D electron Gas in Fock-Darwin states***

- ***Hamiltonian of III-V type Semiconductor***

- ***Effect of Bulk Inversion symmetry (Dresselhaus Effect)***

- ***Effect of Structural Inversion symmetry (Rashba Effect)***

- **Results:**

- ***Illustrations of Asymmetric confining potential in III-V semiconductor (Based on DFT and Finite element method).***

- ***Illustrations of few eigen states and wave functions in this realistic asymmetric confining potentials.***

- ***Calculations of electron g-value in symmetric and Asymmetric confining potentials***

- **Summary and Conclusions**



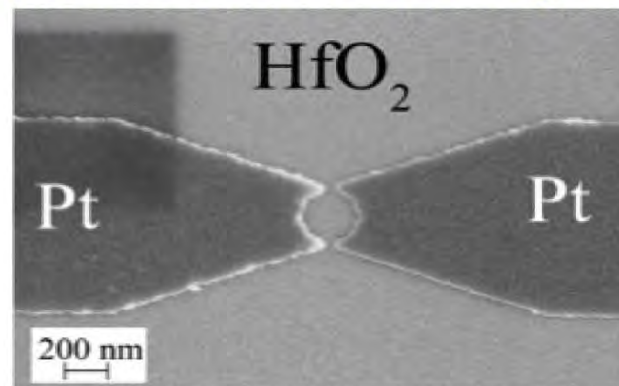
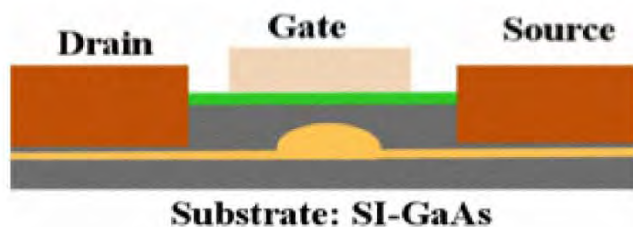
Bandyopadhyay:
Phys. Rev. B 61, 13813 (2000)

Global ac magnetic field



Possible spin-SET prototype (Oktyabrsky)

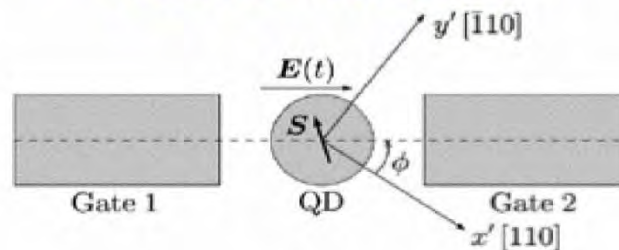
SEM of a 2D-0D heterodimensional prototype



Goal: Development for planar SET prototype using:

- High-k gate stack on InGaAs/AlGaAs structure
- Hetero-dimensional control of 2D-1D-0D electrons
- Eventually self-assembled InAs QD

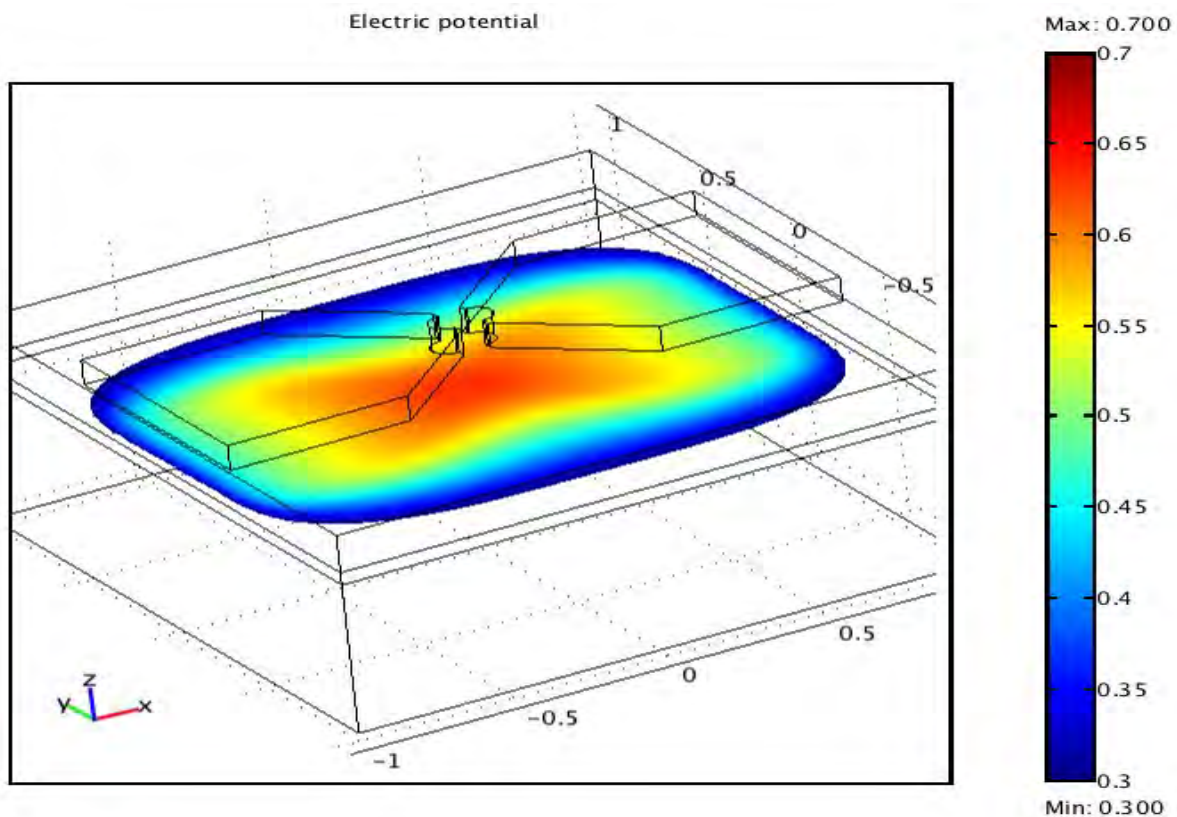
Schematic for EDSR spin control
[Loss et al., PRB 2006]





Results

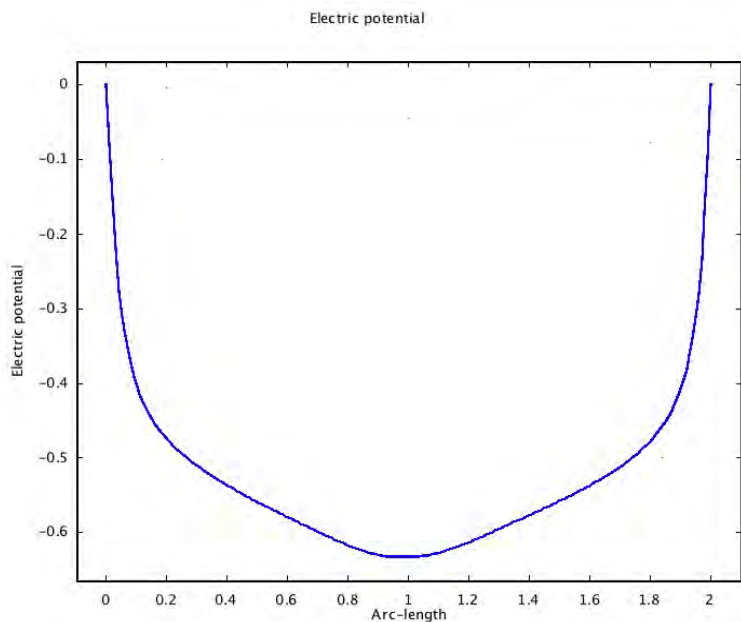
Electric potential in conducting (quantum well) layer



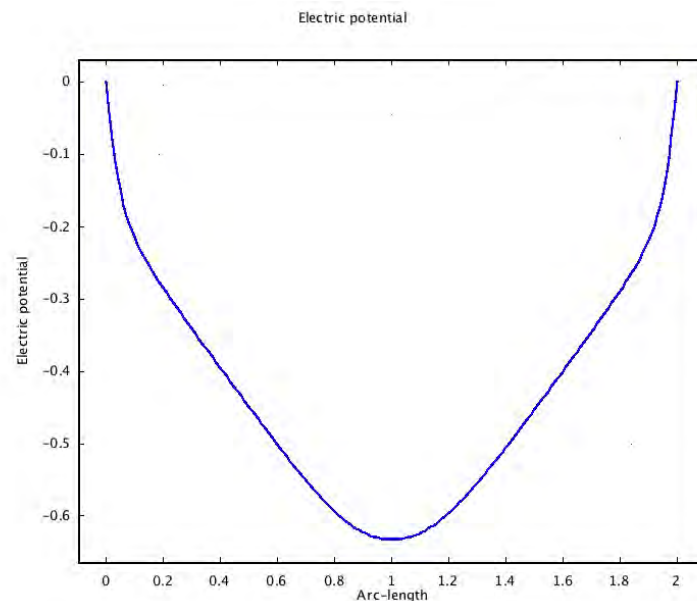


Anisotropic confining potentials

potential along symmetry axis



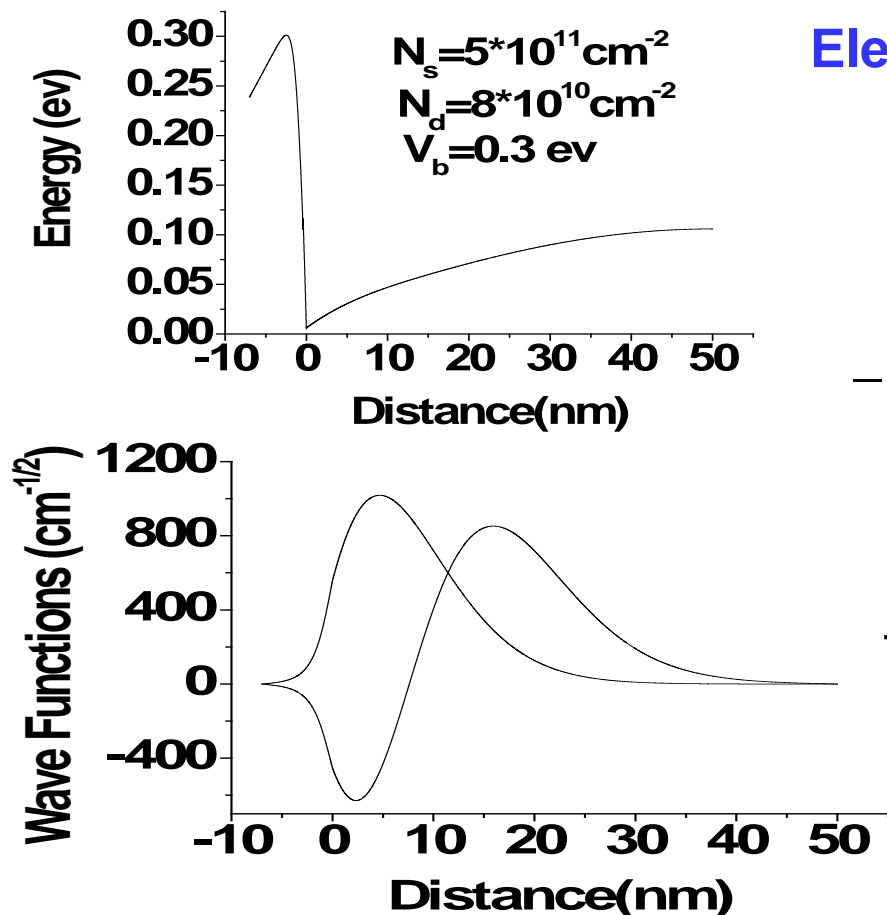
potential normal to symmetry axis





Results: Based on DFT and Finite element method

- Realistic confining potential along growth direction
- Illustration of wave functions in the realistic asymmetric confining potential



Electron moves in an effective potentials

$$V(z) = -e \phi(z) + V_{xc}(z)$$

$$-\frac{\hbar^2}{2} \frac{d}{dz} \frac{1}{m(z)} \frac{d\psi_i(z)}{dz} + V(z)\psi_i(z) = E_i \psi_i(z)$$

$$\frac{d}{dz} \epsilon_0 \kappa(z) \frac{d\phi(z)}{dz} = e \sum N_i \psi_i^2(z) - \rho_I(z)$$

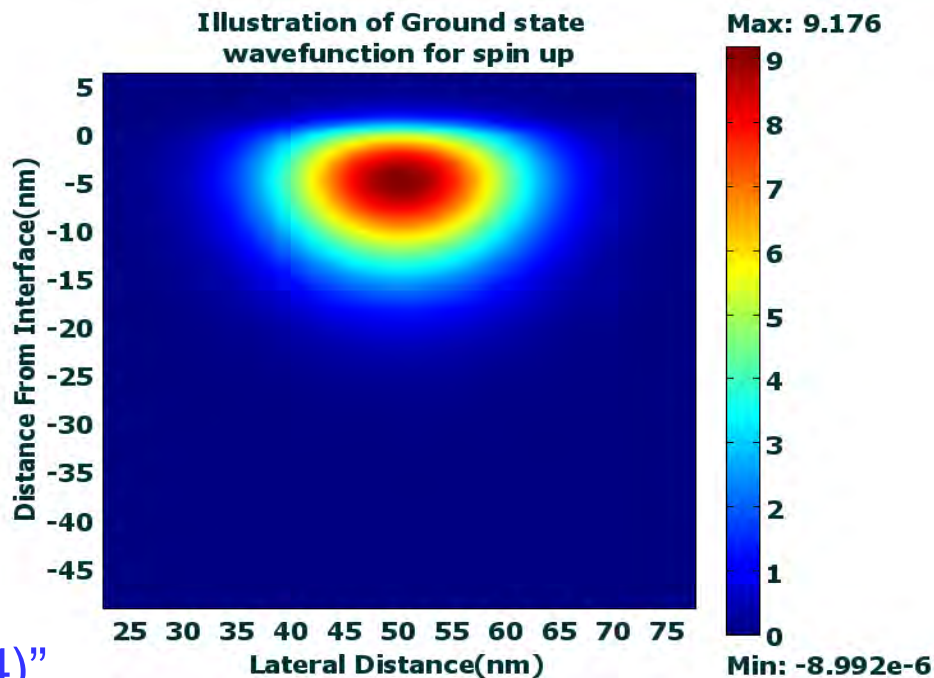
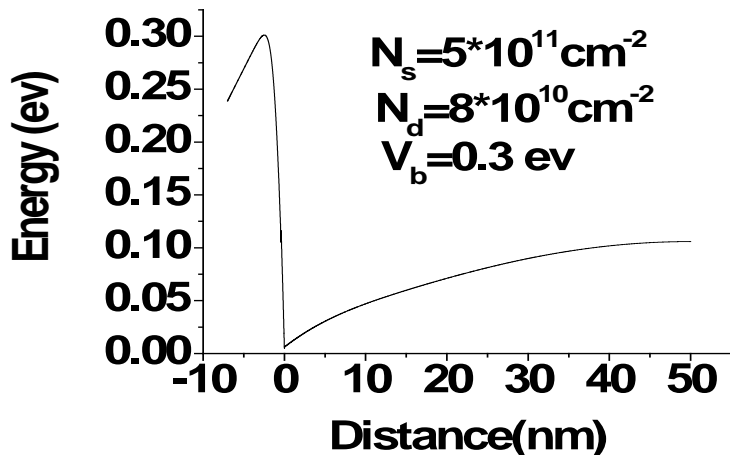
Also See PRB Vol 30,840 (1984)



Results

Strategy: simple to complex

- Use Finite Element Method
- Simple: Solve electrostatic problem with simplified (classical) conductors to determine confining potentials
- Solve Schrödinger equation in fixed potential and effective mass approximation
- Determine wave functions and electric field effects.
- Complex: Self-consistent Schrödinger/Poisson
- Exchange-correlation effects (DFT)



“see also Phys. Rev. B 30, 840 (1984)”



Electrical control of “g” (physical mechanisms)

Wave function overlap: electric fields can “move” the wave function to sample different materials (e.g. GaAs has $g = -0.44$; AlGaAs has $g = +0.4$) see PRB 64, 041307 (2001)

Spin-orbit: (see PRB 68, 155330 (2003))

Dresselhaus: $H_{D1} \propto (-\sigma_x P_x + \sigma_y P_y)$

$$H_{D2} \propto (\sigma_x P_x P_y^2 - \sigma_y P_y P_x^2)$$

Rashba: $H_R \propto E(\sigma_x P_y - \sigma_y P_x)$



Hamiltonian of QD in III-V semiconductor

Hamiltonian for a single electron bound to a heterojunction QD

$$H = H_0 + H_z + H_R + H_{D1} + H_{D2}$$

$$H_0 = \frac{\vec{P}^2}{2m^*} + \frac{1}{2} m^* \omega_0^2 r^2 + \frac{1}{2} g_0 \mu_B \sigma_z B$$

Kinetic momentum $\vec{P} = \vec{p} + \frac{e}{c} \vec{A}$

Canonical momentum $\vec{p} = -i \hbar \left(\partial_x, \partial_y, 0 \right)$

Vector Potential $\vec{A} = \frac{B}{2} (-y, x, 0)$

PRB 68,155330(2003)



Analytical solution of H_0

$$H_0 = \hbar\omega_+ \left(n_+ + \frac{1}{2} \right) + \hbar\omega_- \left(n_- + \frac{1}{2} \right) + \frac{1}{2} g_0 \mu_B \sigma_z B$$

Where $\omega_{\pm} = \Omega \pm \frac{\omega_c}{2}$

renormalized dot frequency $\Omega = \sqrt{\omega_0^2 + \frac{\omega_c^2}{4}}$

Cyclotron frequency $\omega_c = \frac{eB}{m^* c}$

Fock Darwin Radius $\ell = \sqrt{\frac{\hbar}{m^*}} \Omega$

Number Operator $n_{\pm} = a_{\pm}^{\dagger} a_{\pm}$

PRB 68,155330(2003)



$$H = H_0 + H_z + H_R + H_{D1} + H_{D2}$$

2nd term represents the QW confinement in growth direction

$$H_z = \frac{P_z^2}{2m^*} + V(z)$$

$$\begin{aligned} V(z) &= e E z && \textit{For } z \geq 0 \\ &= \infty && \textit{For } z < 0 \end{aligned}$$

PRB 68,155330 (2003)



$$H = H_0 + H_z + H_R + H_{D1} + H_{D2}$$

The structural inversion asymmetry in $V(z)$ leads to the Rashba (spin orbit) interaction

$$H_R = \frac{\alpha_R e E}{\hbar} (\sigma_x P_y - \sigma_y P_x)$$

Phys. Rev. B 68,155330(2003); Phys. Rev. B 55,16293(1997)
Phys. Rev. B 50,8523 (1994)



$$H = H_0 + H_z + H_R + H_{D1} + H_{D2}$$

- Bulk inversion asymmetry is associated with Dresselhaus interaction
- Two Spin orbit terms -Linear in momenta
-Cubic in momenta

$$H_{D1} = \frac{0.7794 \gamma_c k^2}{\hbar} \left(-\sigma_x P_x + \sigma_y P_y \right)$$

$$H_{D2} = \frac{\gamma_c}{\hbar^3} \left(-\sigma_x P_x P_y^2 - \sigma_y P_y P_x^2 \right) + H.c.$$

Phys. Rev. B 68,155330(2003); Phys. Rev. B 55,16293(1997)

Phys. Rev. B 50,8523 (1994)

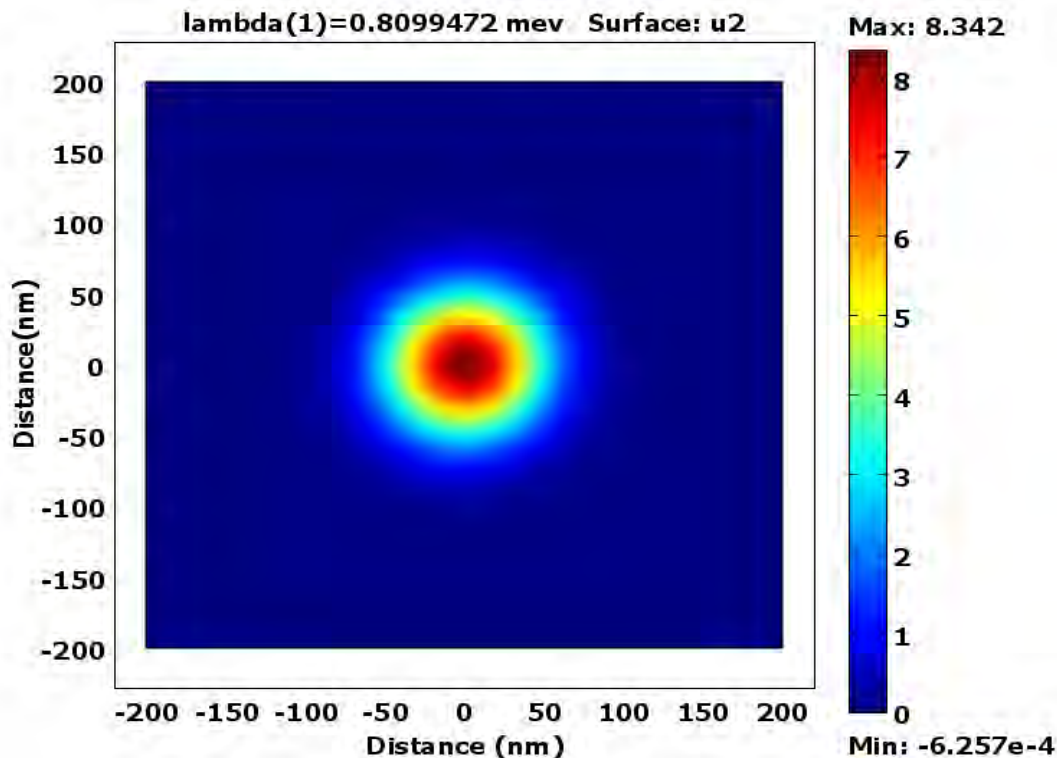


Results

$$H = H_0 + H_z + H_R + H_{D1} + H_{D2}$$

$$H_0 = \frac{\vec{P}_x^2 + \vec{P}_y^2}{2m^*} + \frac{1}{2} m^* \omega_0^2 (x^2 + y^2) + \frac{1}{2} g_0 \mu_B \sigma_z B$$

Illustration of QD in symmetric confining potential including spin

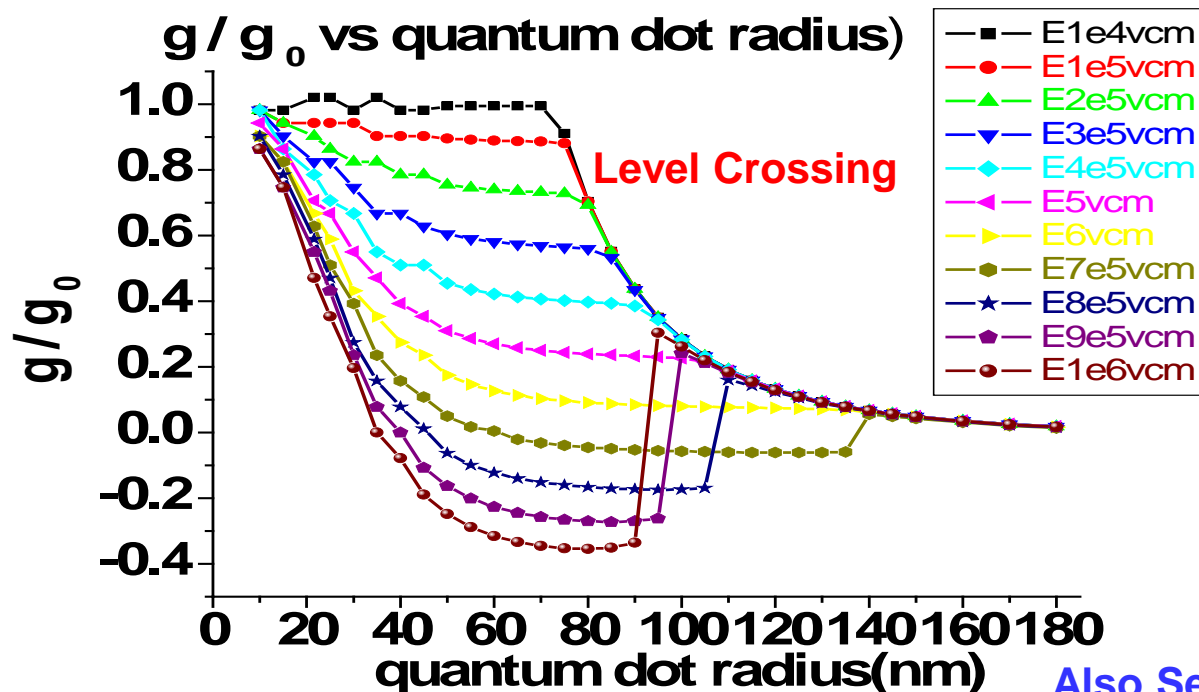




Results *Electric Field Control of Spin in Parabolic Confining Potential*

$$H = H_0 + H_z + H_R + H_{D1} + H_{D2}$$

$$H_0 = \frac{\vec{P}_x^2 + \vec{P}_y^2}{2m^*} + \frac{1}{2} m^* \omega_0^2 (x^2 + y^2) + \frac{1}{2} g_0 \mu_B \sigma_z B$$



$$g = \frac{(E_2 - E_1)}{\mu_B B}$$

$$QD \text{ Radius } \ell_0 = \sqrt{\frac{\hbar}{m^* \omega_0}}$$

Where E_1 and E_2 are Ground and first excited states including spin

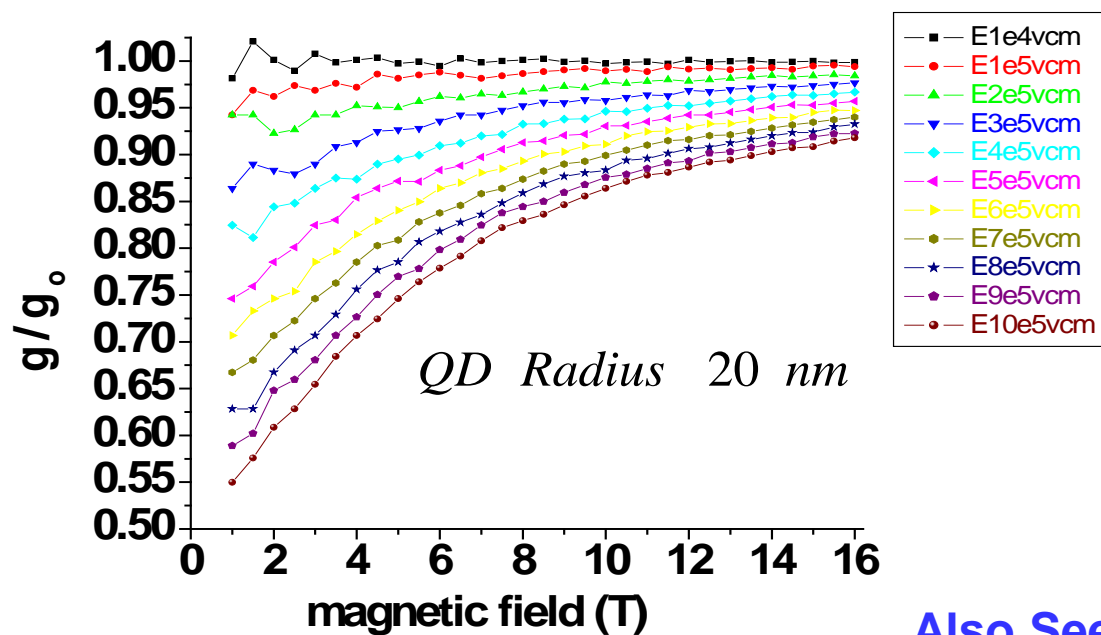
Also See Phys. Rev. B 68, 55330 (2003)



Results *Magnetic Field Control of Spin in Parabolic Potential Confining Potential*

$$H = H_0 + H_z + H_R + H_{D1} + H_{D2}$$

$$H_0 = \frac{\bar{P}_x^2 + \bar{P}_y^2}{2m^*} + \frac{1}{2} m^* \omega_0^2 (x^2 + y^2) + \frac{1}{2} g_0 \mu_B \sigma_z B$$



$$g = \frac{(E_2 - E_1)}{\mu_B B}$$

Also See Phys. Rev. B 68, 55330 (2003)

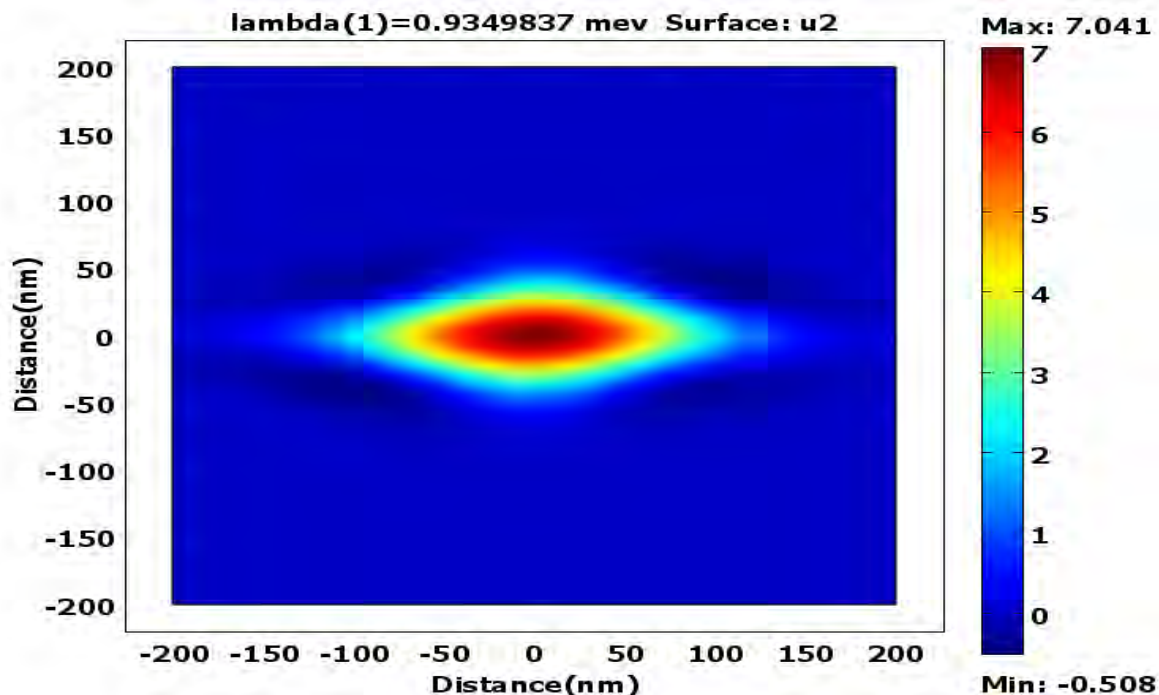


New Results

$$H = H_0 + H_z + H_R + H_{D1} + H_{D2}$$

$$H_0 = \frac{\vec{P}_x^2 + \vec{P}_y^2}{2m^*} + \frac{1}{2} m^* \omega_0^2 (\alpha x^2 + \beta y^2) + \frac{1}{2} g_0 \mu_B \sigma_z B$$

Illustration of QD in Asymmetric confining potential including spin



$$\beta = 2\alpha$$

QD Radius 20 nm



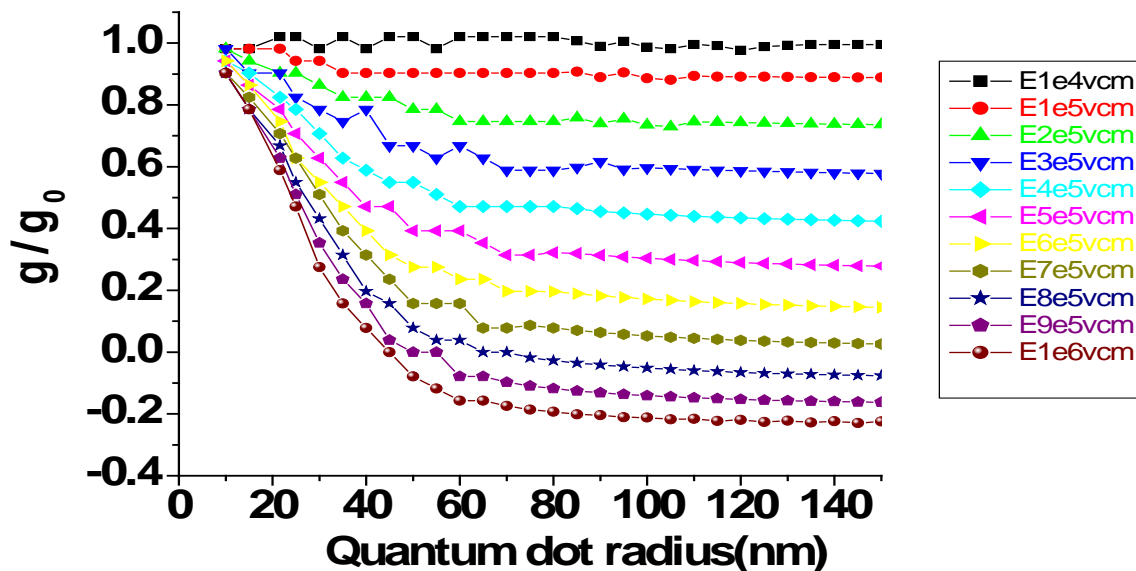
New Results

Electric Field Control of Spin in Asymmetric Confining Parabolic Potential

$$H = H_0 + H_z + H_R + H_{D1} + H_{D2}$$

$$H_0 = \frac{\vec{P}_x^2 + \vec{P}_y^2}{2m^*} + \frac{1}{2} m^* \omega_0^2 (\alpha x^2 + \beta y^2) + \frac{1}{2} g_0 \mu_B \sigma_z B$$

$\beta = 2\alpha$ and QD Radius 120 nm



$$g = \frac{(E_2 - E_1)}{\mu_B B}$$

$$QD \text{ Radius } \ell_0 = \sqrt{\frac{\hbar}{m^* \omega_0}}$$

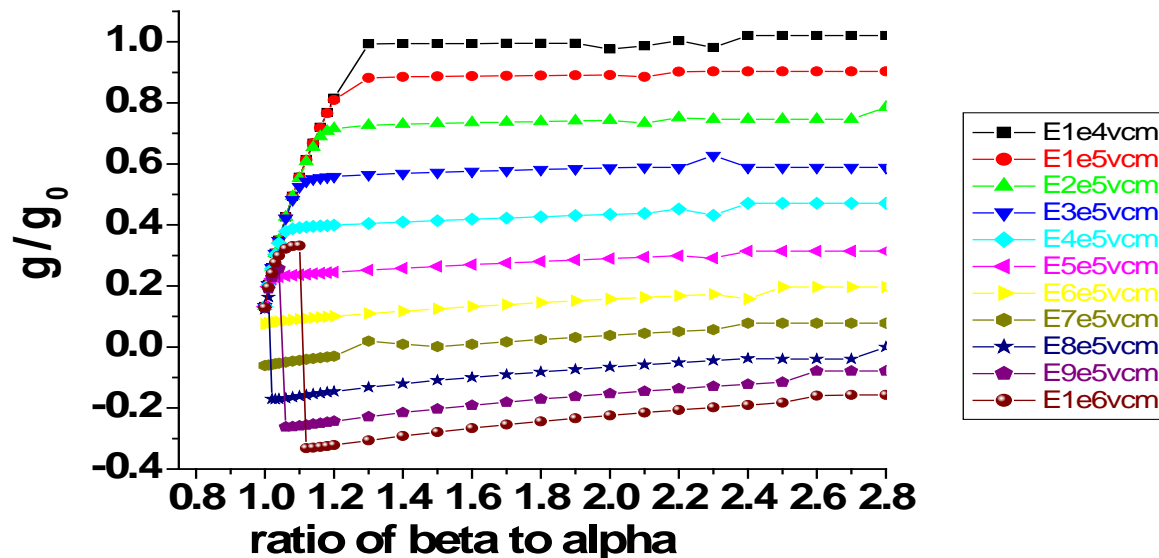


New Results

Electric Field Control of Spin in Asymmetric Confining Parabolic Potential

$$H = H_0 + H_z + H_R + H_{D1} + H_{D2}$$

$$H_0 = \frac{\vec{P}_x^2 + \vec{P}_y^2}{2m^*} + \frac{1}{2} m^* \omega_0^2 (\alpha x^2 + \beta y^2) + \frac{1}{2} g_0 \mu_B \sigma_z B$$



$\alpha = 1, \beta = \text{Variable}$ and
QD Radius 120 nm

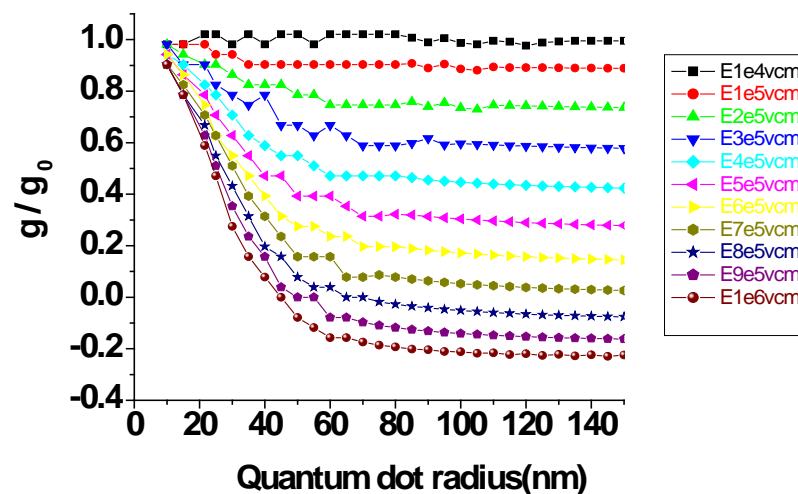
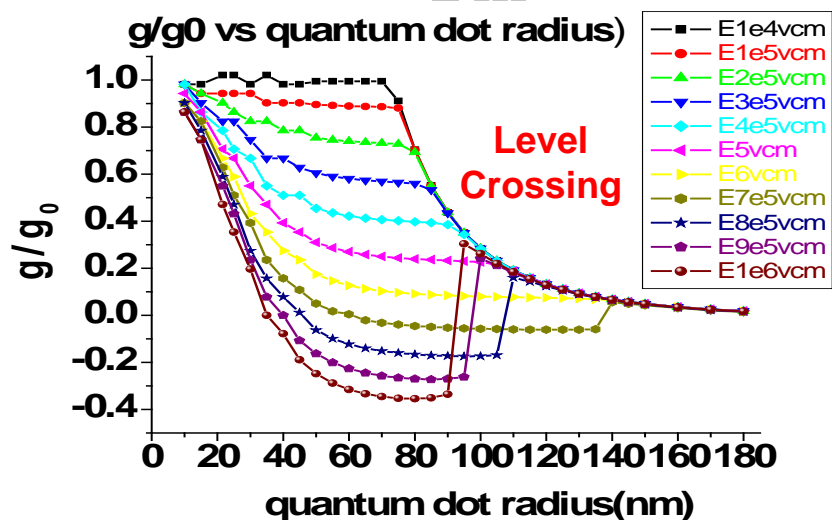
$$g = \frac{(E_2 - E_1)}{\mu_B B}$$



Results Electric Field Control of Spin in Parabolic Confining Potential

$$H = H_0 + H_z + H_R + H_{D1} + H_{D2}$$

$$H_0 = \frac{\vec{P}_x^2 + \vec{P}_y^2}{2m^*} + \frac{1}{2} m^* \omega_0^2 (x^2 + y^2) + \frac{1}{2} g_0 \mu_B \sigma_z B$$



$$g = \frac{(E_2 - E_1)}{\mu_B B} \quad \text{and} \quad QD \text{ Radius } \ell_0 = \sqrt{\frac{\hbar}{m^* \omega_0}}$$

Where E_1 and E_2 are Ground and first excited states including spin

See also Phys. Rev. B 68, 55330 (2003)



Summary and Conclusions

- *A 3D finite-element simulation strategy to study electrical spin control is being pursued*
- *E-field effects on electron “g” value due to spin orbit interactions in symmetric and asymmetric confining potentials have been demonstrated.*
- *Anisotropic confining potentials for realistic device **enhance spin-orbit effects***